

UTC UNISONIC TECHNOLOGIES CO., LTD

8050S

NPN SILICON TRANSISTOR

LOW VOLTAGE HIGH **CURRENT SMALL SIGNAL** NPN TRANSISTOR

DESCRIPTION

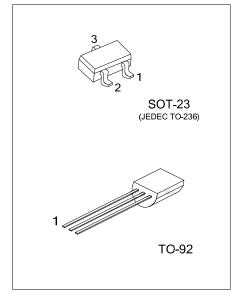
The UTC 8050S is a low voltage high current small signal NPN transistor, designed for Class B push-pull audio amplifier and general purpose applications.

FEATURES

*Collector current up to 700mA *Collector-Emitter voltage up to 20V

* Complementary to UTC 8550S

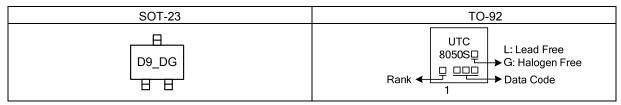
ORDERING INFORMATION



Ordering Number		Dookogo	Pin Assignment			Deaking	
Lead Free	Halogen-Free	Package	1	2	3	Packing	
-	8050SG-x-AE3-R	SOT-23	ш	В	С	Tape Reel	
8050SL-x-T92-B	8050SG-x-T92-B	TO-92	ш	С	В	Таре Вох	
8050SL-x-T92-K	8050SG-x-T92-K	TO-92	ш	С	В	Bulk	
Note: Pin Assignment: B: Base	C: Collector E: Emitter						

8050SG-x-AE3-R (1)Packing Type (2)Package Type (3)Rank (4)Green Package	 (1) B: Tape Box, K: Bulk, R: Tape Reel (2) AE3: SOT-23, T92: TO-92 (3) x: refer to Classification of h_{FE2} (4) G: Halogen Free and Lead Free, L: Lead Free 	
	(4) G: Halogen Free and Lead Free, L: Lead Free	

MARKING



■ **ABSOLUTE MAXIMUM RATING** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	30	V
Collector-Emitter Voltage		V _{CEO}	20	V
Emitter-Base Voltage		V _{EBO}	5	V
Collector Current		lc	700	mA
Collector Dissipation(T _A =25°C)	SOT-23	Pc	350	mW
	TO-92		1	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV _{CBO}	I _C = 100μA, I _E = 0	30			V
BV_{CEO}	I _C = 1mA, I _B = 0	20			V
BV_{EBO}	I _E = 100μA, I _C =0	5			V
I _{CBO}	$V_{CB} = 30V, I_{E} = 0$			1	uA
I _{EBO}	$V_{EB} = 5V, I_{C} = 0$			100	nA
h _{FE1}	V _{CE} = 1V, I _C = 1mA	100			
h _{FE2}	V _{CE} = 1V, I _C = 150 mA	120		400	
h _{FE3}	V _{CE} = 1V, I _C = 500mA	40			
V _{CE(SAT)}	I _C = 500mA, I _B = 50mA			0.5	V
V _{BE(SAT)}	I _C = 500mA, I _B = 50mA			1.2	V
V _{BE(SAT)}	V _{CE} = 1V, I _C = 10mA			1.0	V
f⊤	V _{CE} = 10V, I _C = 50mA	100			MHz
Cob	V _{CB} = 10V, I _E = 0, f = 1MHz		9.0		pF
	$\begin{array}{c} BV_{CBO}\\ BV_{CEO}\\ BV_{EBO}\\ I_{CBO}\\ I_{EBO}\\ h_{FE1}\\ h_{FE2}\\ h_{FE3}\\ V_{CE(SAT)}\\ V_{BE(SAT)}\\ V_{BE(SAT)}\\ f_{T} \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

CLASSIFICATION OF h_{FE2}

RANK	С	D	E
RANGE	120-200	160-300	280-400

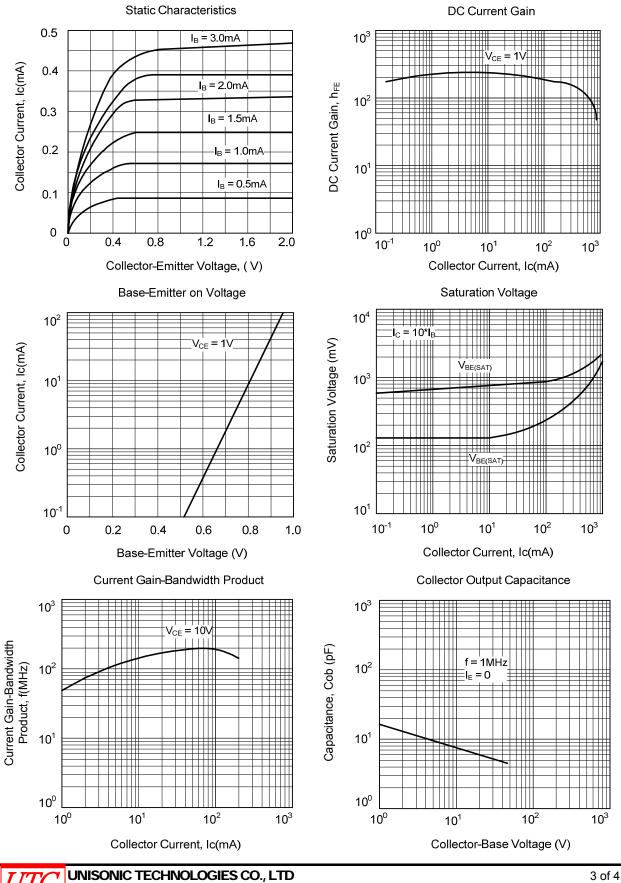


8050S

NPN SILICON TRANSISTOR

TYPICAL CHARACTERISTICS

www.unisonic.com.tw



QW-R206-001.I

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